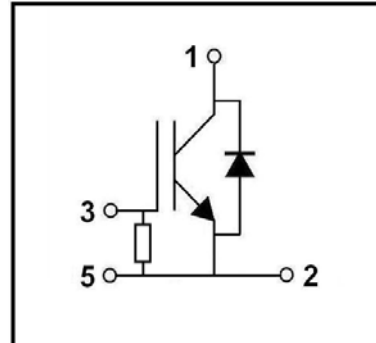


FEATURES

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- With Fast Free-Wheeling Diodes
- 10K Ω Gate Protected Resistance Inside

APPLICATIONS

- Inverter
- Convertor
- Welder
- SMPS and UPS
- Induction Heating



ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage		1200	V
V_{GES}	Gate - Emitter Voltage		± 20	V
I_C	DC Collector Current	$T_C=25^\circ\text{C}$	900	A
		$T_C=80^\circ\text{C}$	600	A
I_{Cpuls}	Pulsed Collector Current	$T_C=25^\circ\text{C}, t_p=1\text{ms}$	1800	A
		$T_C=80^\circ\text{C}, t_p=1\text{ms}$	1200	A
P_{tot}	Power Dissipation Per IGBT		3125	W
T_J	Junction Temperature Range		-40 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-40 to +125	$^\circ\text{C}$
V_{isol}	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
Free-Wheeling Diode				
V_{RRM}	Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^\circ\text{C}$	600	A
		$T_C=80^\circ\text{C}$	400	A
$I_{F(RMS)}$	RMS Forward Current		600	A
I_{FSM}	Non-Repetitive Surge	$T_J=45^\circ\text{C}, t=10\text{ms}, \text{Sine}$	4000	A
	Forward Current	$T_J=45^\circ\text{C}, t=8.3\text{ms}, \text{Sine}$	4400	A

MMG600KR120U

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
IGBT						
V _{GE(th)}	Gate - Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =24mA	5	6.2	7	V
V _{CE(sat)}	Collector - Emitter Saturation Voltage	I _C =600A, V _{GE} =15V, T _J =25°C		1.9		V
		I _C =600A, V _{GE} =15V, T _J =125°C		2.1		V
I _{CES}	Collector Leakage Current	V _{CE} =1200V, V _{GE} =0V, T _J =25°C			4	mA
		V _{CE} =1200V, V _{GE} =0V, T _J =125°C			40	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V, V _{GE} =±20V		2		mA
Q _{ge}	Gate Charge	V _{CC} =600V, I _C =600A, V _{GE} =±15V		6120		nC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=1MHz		42.2		nF
C _{oes}	Output Capacitance			2.82		nF
C _{res}	Reverse Transfer Capacitance			1.88		nF
t _{d(on)}	Turn - on Delay Time	V _{CC} =600V, I _C =600A		190		ns
t _r	Rise Time	R _G =1.7 Ω, V _{GE} =±15V		60		ns
t _{d(off)}	Turn - off Delay Time	T _J =25°C		460		ns
t _f	Fall Time	Inductive Load		55		ns
t _{d(on)}	Turn - on Delay Time	V _{CC} =600V, I _C =600A		220		ns
t _r	Rise Time	R _G =1.7 Ω, V _{GE} =±15V		60		ns
t _{d(off)}	Turn - off Delay Time	T _J =125°C		530		ns
t _f	Fall Time	Inductive Load		75		ns
E _{on}	Turn - on Switching Energy	V _{CC} =600V, I _C =600A, T _J =25°C		44.8		mJ
		R _G =1.7 Ω, T _J =125°C		66.8		mJ
E _{off}	Turn - off Switching Energy	V _{GE} =±15V, T _J =25°C		39.2		mJ
		Inductive Load, T _J =125°C		61.2		mJ
Free-Wheeling Diode						
V _F	Forward Voltage	I _F =400A, V _{GE} =0V, T _J =25°C		1.8	2.44	V
		I _F =400A, V _{GE} =0V, T _J =125°C		1.5	2.20	V
t _{rr}	Reverse Recovery Time	I _F =400A, V _R =800V		450		ns
I _{RRM}	Max. Reverse Recovery Current	di _F /dt=-1000A/μs		150		A
Q _{rr}	Reverse Recovery Charge	T _J =125°C		41		μC

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R _{thJC}	Junction-to-Case Thermal Resistance	Per IGBT			0.04	K /W
R _{thJCD}	Junction-to-Case Thermal Resistance	Per Inverse Diode			0.09	K /W
Torque	Module-to-Sink	Recommended (M6)	3		5	N · m
Torque	Module Electrodes	Recommended (M6)	2.5		5	N · m
Torque	Module Electrodes	Recommended (M4)	0.7		1.1	N · m
Weight				325		g

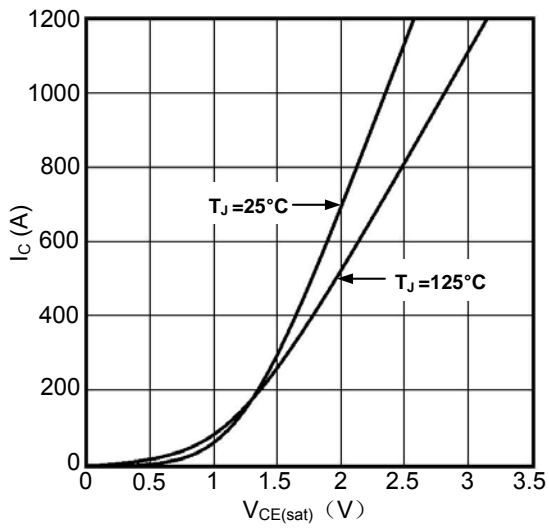


Figure1. Typical Output characteristics

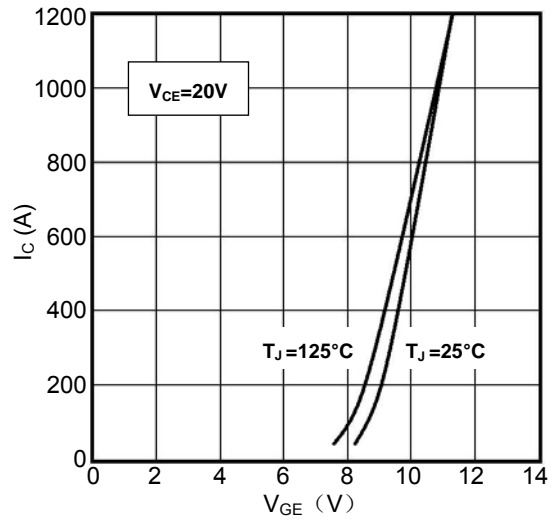


Figure2. Typical Transfer characteristics

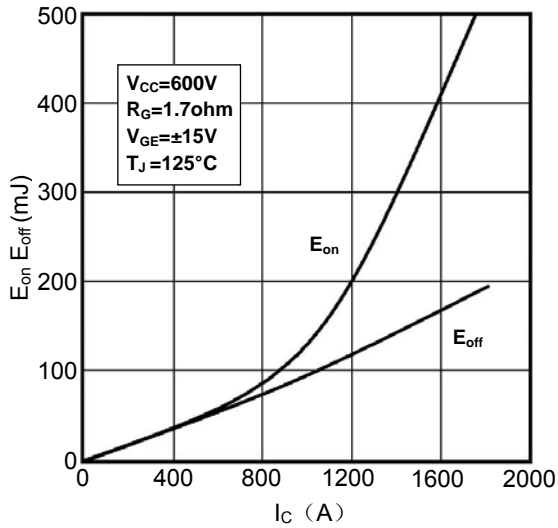


Figure3. Switching Energy vs. Collector Current

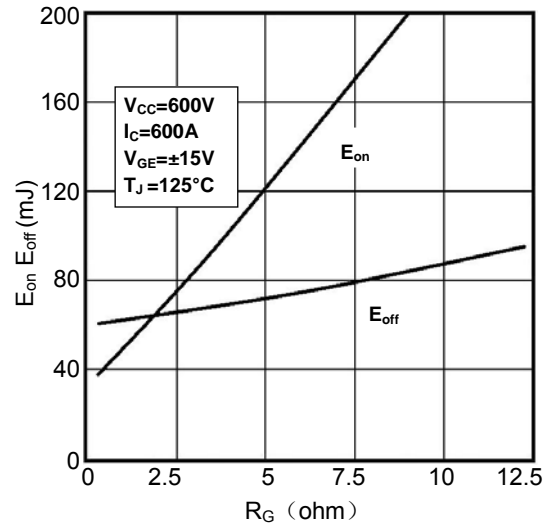


Figure4. Switching Energy vs. Gate Resistor

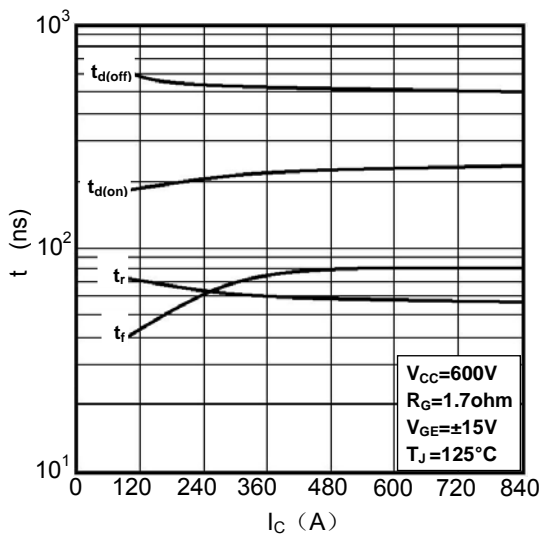


Figure5. Switching Times vs. Collector Current

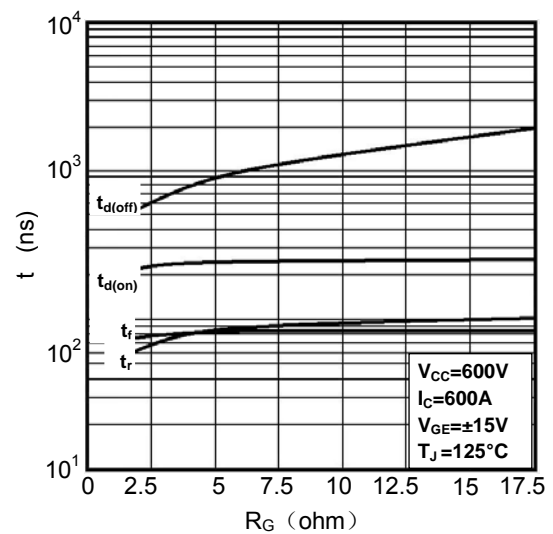


Figure6. Switching Times vs. Gate Resistor

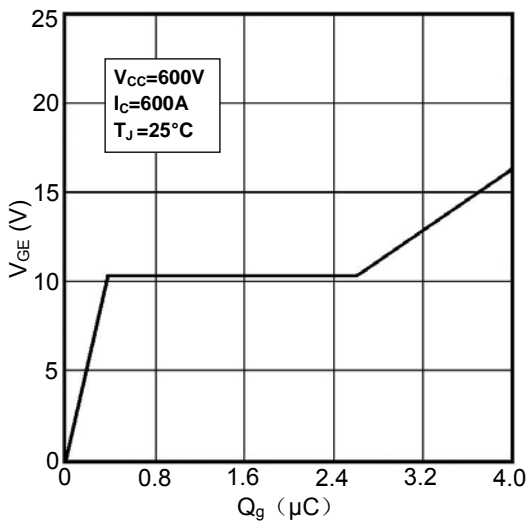


Figure7. Gate Charge characteristics

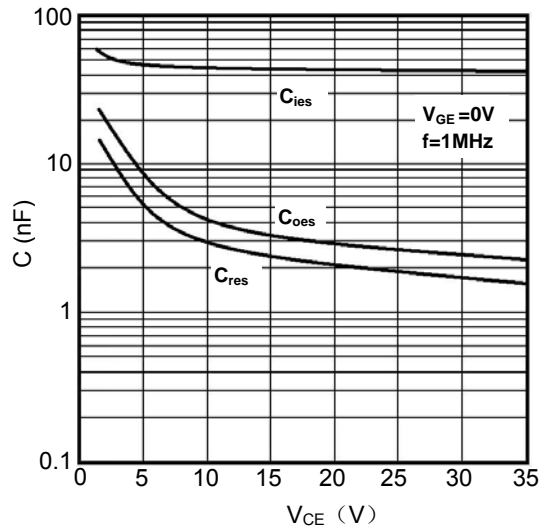


Figure8. Typical Capacitances vs. V_{CE}

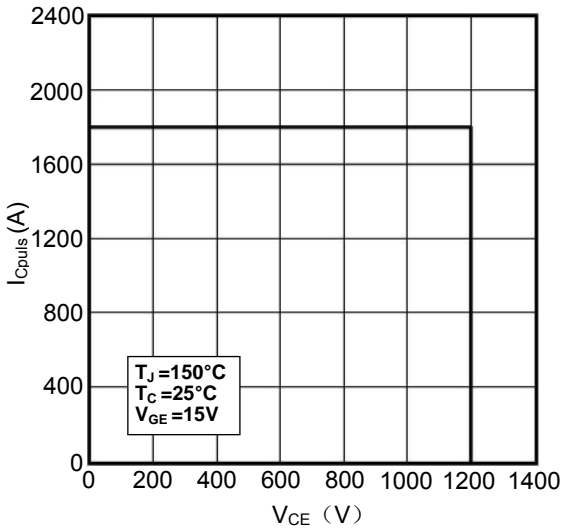


Figure9. Reverse Biased Safe Operating Area

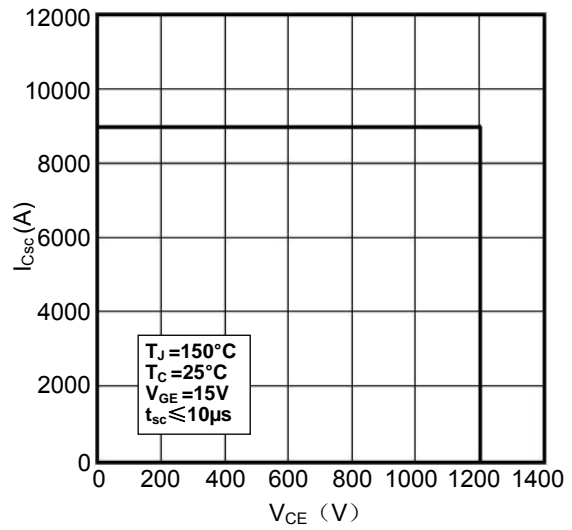


Figure10. Short Circuit Safe Operating Area

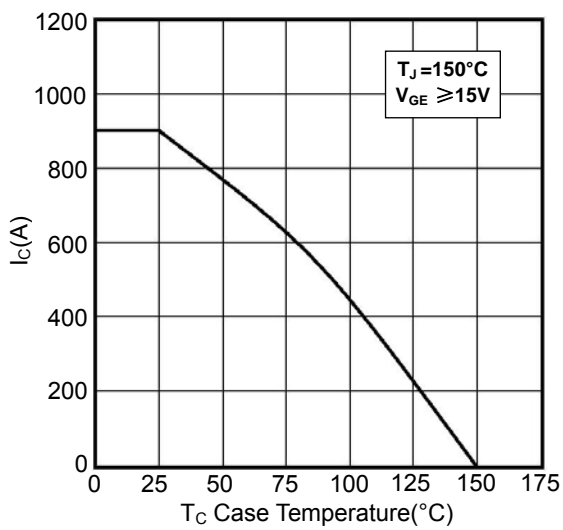


Figure11. Rated Current vs. T_C

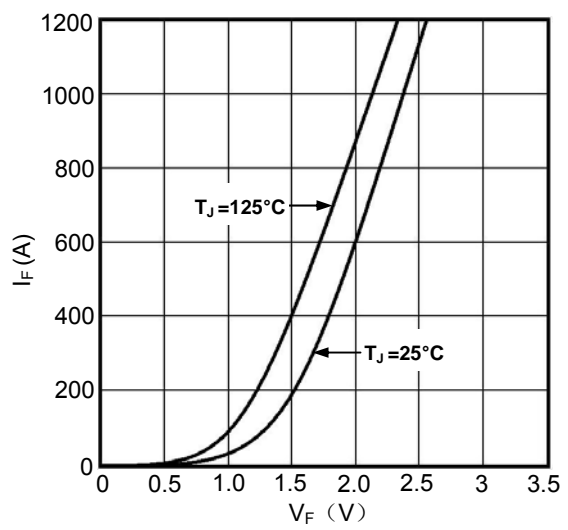
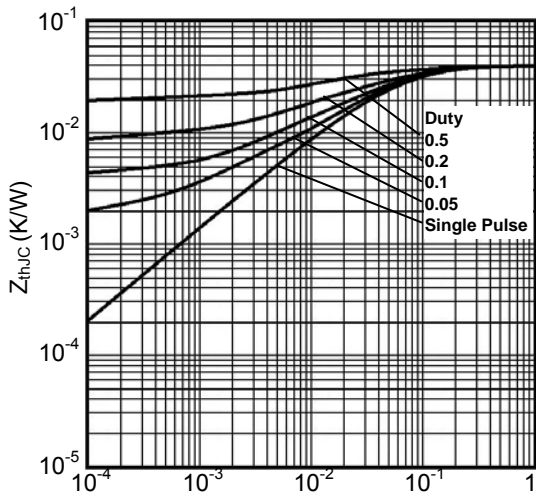
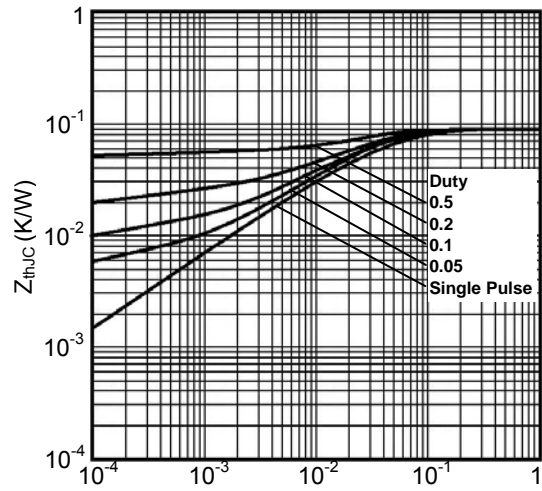


Figure12. Diode Forward Characteristics



Rectangular Pulse Duration (seconds)
Figure13. Transient Thermal Impedance of IGBT



Rectangular Pulse Duration (seconds)
Figure14. Transient Thermal Impedance of Diode

